

### Digital Transistors (BRT) R1 = 100 k $\Omega$ , R2 = $\infty$ k $\Omega$

PNP Transistors with Monolithic Bias Resistor Network

### MUN2141, MMUN2141L, MUN5141, DTA115TE, DTA115TM3, NSBA115TF3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

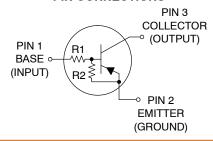
### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current - Continuous	Ic	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	5	Vdc

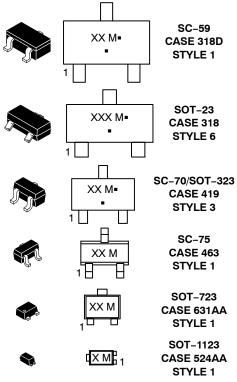
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

### **PIN CONNECTIONS**



### **MARKING DIAGRAMS**



XXX = Specific Device Code

M = Date Code\*

Pb-Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

<sup>\*</sup>Date Code orientation may vary depending upon manufacturing location.

**Table 1. ORDERING INFORMATION** 

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2141T1G	6Y	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2141LT1G	ACH	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5141T1G	6T	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA115TET1G	6U	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA115TM3T5G	7G	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBA115TF3T5G	Q (90°)*	SOT-1123 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\* (</sup>xx°) = Degree rotation in the clockwise direction.

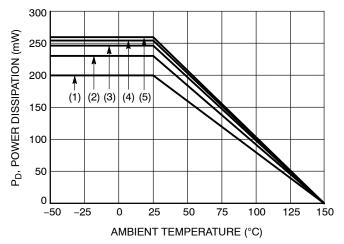


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

**Table 2. THERMAL CHARACTERISTICS** 

	Characteristic	Symbol	Max	Unit
THERMAL CHARACTERIS	STICS (SC-59) (MUN2141)			
Total Device Dissipation		P <sub>D</sub>		
$T_A = 25^{\circ}C$	(Note 1)		230	mW
Derate above 25°C	(Note 2) (Note 1)		338 1.8	mW/°C
Derate above 25 O	(Note 1)		2.7	illivv, O
Thermal Resistance,	(Note 1)	$R_{ heta JA}$	540	°C/W
Junction to Ambient	(Note 2)		370	
Thermal Resistance,	(Note 1)	$R_{ hetaJL}$	264	°C/W
Junction to Lead	(Note 2)		287	
Junction and Storage Temp		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERIS	STICS (SOT-23) (MMUN2141L)			7
Total Device Dissipation $T_A = 25^{\circ}C$	(Note 1)	P <sub>D</sub>	246	mW
1A = 23 G	(Note 2)		400	11144
Derate above 25°C	(Note 1)		2.0	mW/°C
	(Note 2)		3.2	
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	508 311	°C/W
	. ,			00044
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	174 208	°C/W
Junction and Storage Temp	perature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERIS	STICS (SC-70/SOT-323) (MUN5141)	9	·	l
Total Device Dissipation		$P_{D}$		
T <sub>A</sub> = 25°C	(Note 1)	J . D	202	mW
,,	(Note 2)		310	
Derate above 25°C (Note	(Note 1) 2)		1.6 2.5	mW/°C
Thermal Resistance,	(Note 1)	$R_{ hetaJA}$	618	°C/W
Junction to Ambient	(Note 2)	Т	403	0,,,,
Thermal Resistance,	(Note 1)	$R_{ hetaJL}$	280	°C/W
Junction to Lead	(Note 2)		332	
Junction and Storage Temp	perature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERIS	STICS (SC-75) (DTA115TE)			
Total Device Dissipation	(Alata 4)	P <sub>D</sub>	000	
$T_A = 25^{\circ}C$	(Note 1) (Note 2)		200 300	mW
Derate above 25°C	(Note 2)		1.6	mW/°C
	(Note 2)		2.4	,
Thermal Resistance,	(Note 1)	$R_{ hetaJA}$	600	°C/W
Junction to Ambient	(Note 2)		400	
Junction and Storage Temp	perature Range	$T_{J}$ , $T_{stg}$	-55 to +150	°C
THERMAL CHARACTERIS	STICS (SOT-723) (DTA115TM3)			
Total Device Dissipation	(Note 1)	P <sub>D</sub>	260	m\A/
$T_A = 25^{\circ}C$	(Note 1) (Note 2)		260 600	mW
Derate above 25°C	(Note 1)		2.0	mW/°C
	(Note 2)		4.8	, 3
Thermal Resistance,	(Note 1)	$R_{ hetaJA}$	480	°C/W
Junction to Ambient	(Note 2)		205	
Junction and Storage Temp	perature Range	$T_J,T_stg$	-55 to +150	°C

- FR-4 @ Minimum Pad.
   FR-4 @ 1.0 x 1.0 Inch Pad.
   FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
   FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 2. THERMAL CHARACTERISTICS** 

	Characteristic	Symbol	Max	Unit			
THERMAL CHARACTERISTICS (SOT-1123) (NSBA115TF3)							
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4)	P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C			
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{ hetaJA}$	493 421	°C/W			
Thermal Resistance, Junction to Lead (Note 3)		$R_{ hetaJL}$	193	°C/W			
Junction and Storage Tem	perature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C			

- FR-4 @ Minimum Pad.
   FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
   FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ( $T_A = 25$ °C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	•		
Collector-Base Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	_	100	nAdc
Collector–Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I <sub>CEO</sub>	_	-	500	nAdc
Emitter–Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_C = 0)$	I <sub>EBO</sub>	_	-	0.1	mAdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0)	V <sub>(BR)</sub> CBO	50	_	-	Vdc
Collector–Emitter Breakdown Voltage (Note 5) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	50	-	_	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	160	350	-	
Collector-Emitter Saturation Voltage (Note 5) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA)	V <sub>CE(sat)</sub>	_	-	0.25	Vdc
Input Voltage (off) (V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 100 $\mu$ A)	V <sub>i(off)</sub>	_	0.6	0.5	Vdc
Input Voltage (on) ( $V_{CE} = 0.3 \text{ V}, I_{C} = 1.0 \text{ mA}$ )	V <sub>i(on)</sub>	1.5	1.0	_	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 2.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	_	-	0.2	Vdc
Output Voltage (off) $(V_{CC} = 5.0 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	70	100	130	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	-	-	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

# TYPICAL CHARACTERISTICS MUN2141, MMUN2141, MUN5141, DTA115TE, DTA115TM3, NSBA115TF3

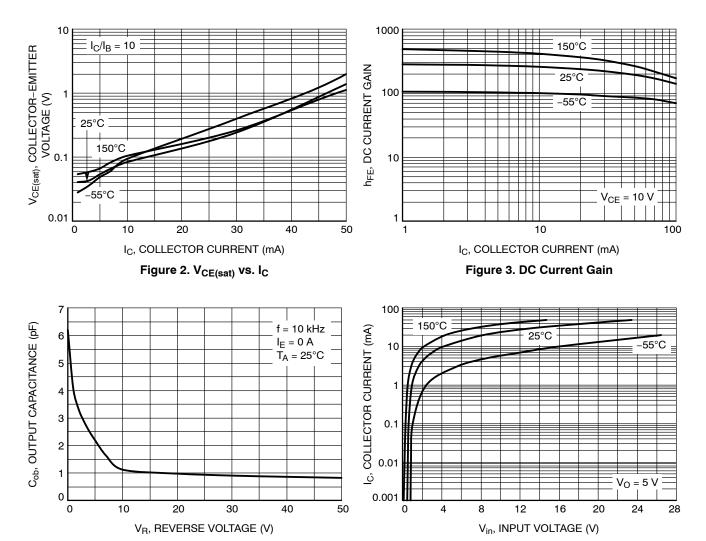


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

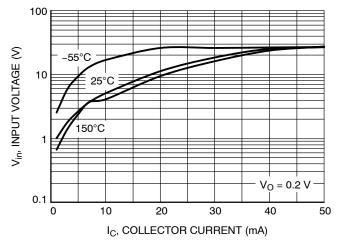


Figure 6. Input Voltage vs. Output Current

### **PACKAGE DIMENSIONS**



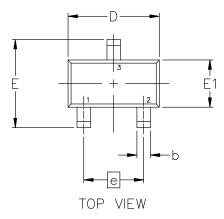
SC-59-3 2.90x1.50x1.15, 1.90P CASE 318D ISSUE J

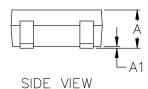
**DATE 15 FEB 2024** 

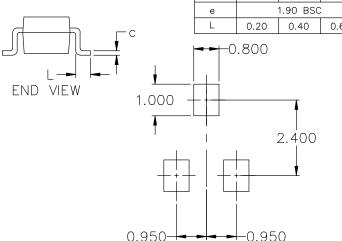
### NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- 2. ALL DIMENSION ARE IN MILLIMETERS.

	MILLIMETERS				
DIM	MIN.	NOM.	MAX.		
Α	1.00	1.15	1.30		
A1	0.01	0.06	0.10		
Ф	0.35	0.43	0.50		
C	0.09	0.14	0.18		
D	2.70	2.90	3.10		
E	2.50	2.80	3.00		
E1	1.30	1.50	1.70		
е	1.90 BSC				
L	0.20	0.40	0.60		







### RECOMMENDED MOUNTING FOOTPRINT\*

\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.





XXX = Specific Device Code

M = Date Code

= Pb-Free Package\*

(\*Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

 STYLE 1:
 STYLE 2:
 STYLE 3:

 PIN 1. BASE
 PIN 1. ANODE
 PIN 1. ANODE

 2. EMITTER
 2. N.C.
 2. ANODE

 3. COLLECTOR
 3. CATHODE
 3. CATHODE

 STYLE 4:
 STYLE 5:
 STYLE 6:

 PIN 1. CATHODE
 PIN 1. CATHODE
 PIN 1. ANODE

 2. N.C.
 2. CATHODE
 2. CATHODE

 3. ANODE
 3. ANODE
 3. ANODE/CATHODE

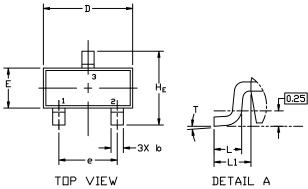




**SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

# GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

### **STYLES ON PAGE 2**

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



### **SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	N	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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SC-70 (SOT-323) **CASE 419** ISSUE R

END VIEW

**DATE 11 OCT 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	M:	ILLIMETE	RS		INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2	0.70 REF				0.028 BS	C	
b	0.30	0.35	0.40	0.012	0.014	0.016	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.00	2.20	0.071	0.080	0.087	
E	1.15	1.24	1.35	0.045	0.049	0.053	
е	1.20	1.30	1.40	0.047	0.051	0.055	
e1	0.65 BSC				0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022	
HE	2.00	2.10	2.40	0.079	0.083	0.095	



### **GENERIC MARKING DIAGRAM**

SIDE VIEW



= Specific Device Code XX

М = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	<ol><li>CATHODE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1

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### SC75-3 1.60x0.80x0.80, 1.00P **CASE 463 ISSUE H**

**DATE 01 FEB 2024** 

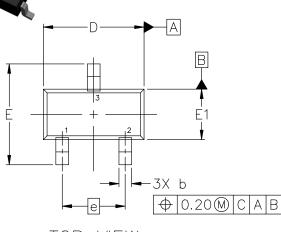
### NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

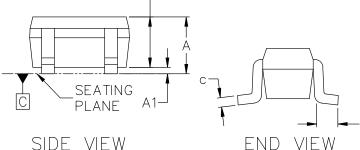
DIM	MILLIMETERS			
DIIVI	MIN.	NOM.	MAX.	
А	0.70	0.80	0.90	
A1	0.00	0.05	0.10	
A2	0.80 REF.			
b	0.15	0.20	0.30	
С	0.10	0.15	0.25	
D	1.55	1.60	1.65	
E	1.50	1.60	1.70	
E1	0.70	0.80	0.90	
е	1.00 BSC			
L	0.10	0.15	0.20	

0.356

0.787



VIEW



A2

SIDE VIEW

### **GENERIC MARKING DIAGRAM\***



XX= Specific Device Code

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. EMITTER

PIN 1. CATHODE 2. CATHODE

3. ANODE

STYLE 4:

STYLE 2: PIN 1. ANODE 2. N/C 3. COLLECTOR 3. CATHODE

STYLE 5:

PIN 1. GATE 2. SOURCE

3. DRAIN

STYLE 3: PIN 1. ANODE 2. ANODE

3. CATHODE

1.000 RECOMMENDED MOUNTING FOOTPRINT\*

1.803

0.508

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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DESCRIPTION:	SC75-3 1.60x0.80x0.80, 1.00P		PAGE 1 OF 1

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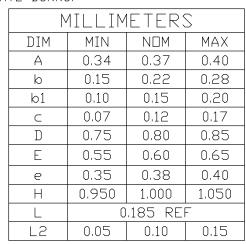


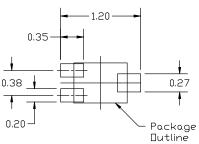
### SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

**DATE 18 JAN 2024** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
  OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



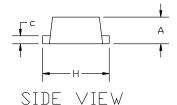


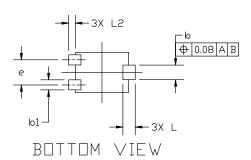
### RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download th e □N Semiconductor Soldering and Mounting Techniques Reference manual, S□L□ERRM/□.

- I	B I
	E U

THP VIFW





### GENERIC MARKING DIAGRAM\*



X = Specific Device Code

M = Date Code

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

YLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
<ol><li>EMITTER</li></ol>	2. N/C	2. ANODE	2. CATHODE	<ol><li>SOURCE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	3. ANODE	3. DRAIN

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-1123 0.80x0.60x0.37,	SOT-1123 0.80x0.60x0.37, 0.35P		

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MILLIMETERS

 $N\square M$ .

0.50



### SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

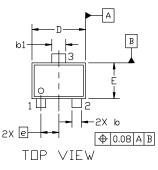
**DATE 24 JAN 2024** 

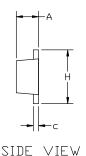
MAX.

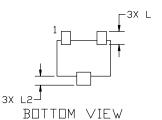
0.55

### NOTES:

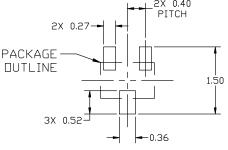
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.







b	0.15	0.21	0.27	
b1	0.25	0.31	0.37	
С	0.07	0.12	0.17	
D	1.15	1.20	1.25	
Е	0.75	0.80	0.85	
е	0.40 BSC			
Н	1.15 1.20 1.2		1.25	
L	0.29 REF			
L2	0.15 0.20		0.25	
0.27   2X 0.40 PITCH				



DIM

Α

MIN.

0.45

### RECOMMENDED MOUNTING FUUTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

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PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
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<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>DRAIN</li></ol>

DOCUMENT NUMBER:	98AON12989D	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED	
DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P		PAGE 1 OF 1

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